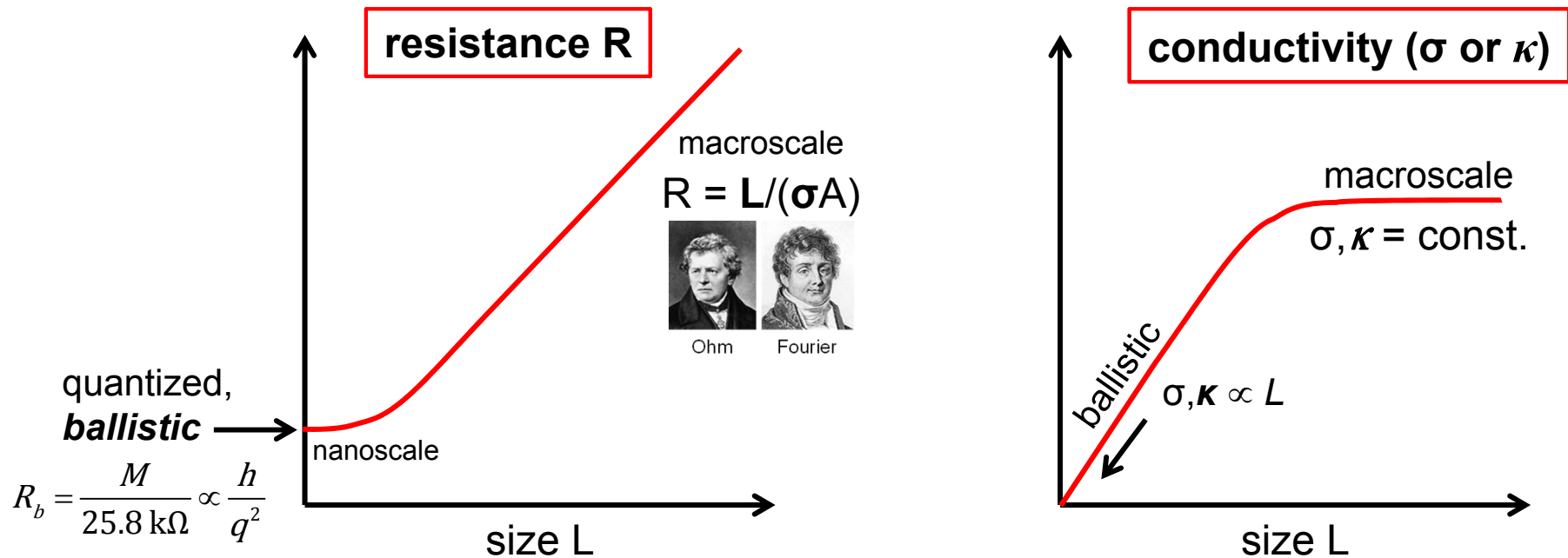


# Conductance Quantization

- One-dimensional ballistic/coherent transport
- Landauer theory
- The role of contacts
- Quantum of electrical and thermal conductance
- One-dimensional Wiedemann-Franz law

# “Ideal” Electrical Resistance in 1-D



- Macroscale,  $R$  is additive:  $1 + 1 = 2$
- **Nanoscale**,  $R$  is quantized:  $1 + 1 = 1$ 
  - Occurs when system size is comparable to the electron or phonon (heat) wavelengths and collision distance (10-100 nm)
  - Both electrical and thermal resistance can be **quasi-ballistic**

# Charge & Energy Current Flow in 1-D

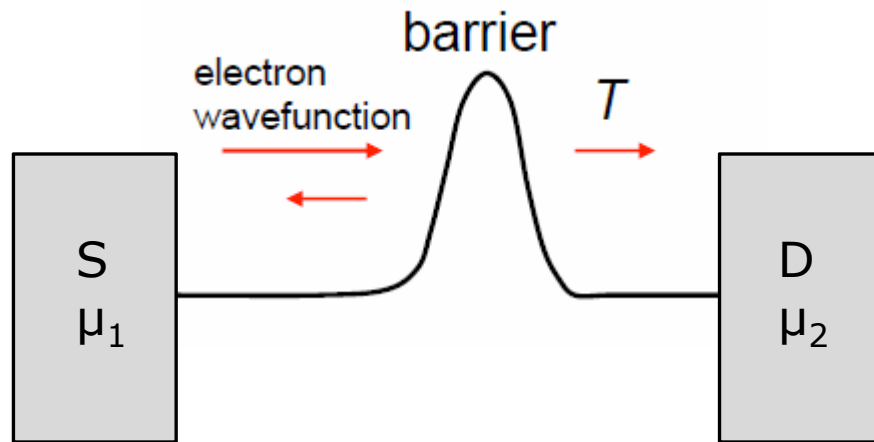
- Remember (net) current  $J_x \approx x \times n \times v$  where  $x = q$  or  $E$

$$J_q = q \sum_k n_k \mathbf{v}_k = q \sum_k [g_k f_k] \mathbf{v}_k \quad \rightarrow \quad J_q = q \int_k g_k \underbrace{f_k}_{\text{Net contribution}} \mathbf{v}_k dk$$

$$J_E = \sum_k E_k n_k \mathbf{v}_k = \sum_k E_k [g_k f_k] \mathbf{v}_k \quad \rightarrow \quad J_E = \int_k E_k g_k f_k \mathbf{v}_k dk$$

- Let's focus on charge current flow, for now
- Convert to integral over energy, use Fermi distribution

# Conductance as Transmission



$$J_q = q \int_k g_k f_k T_k \mathbf{v}_k dk$$

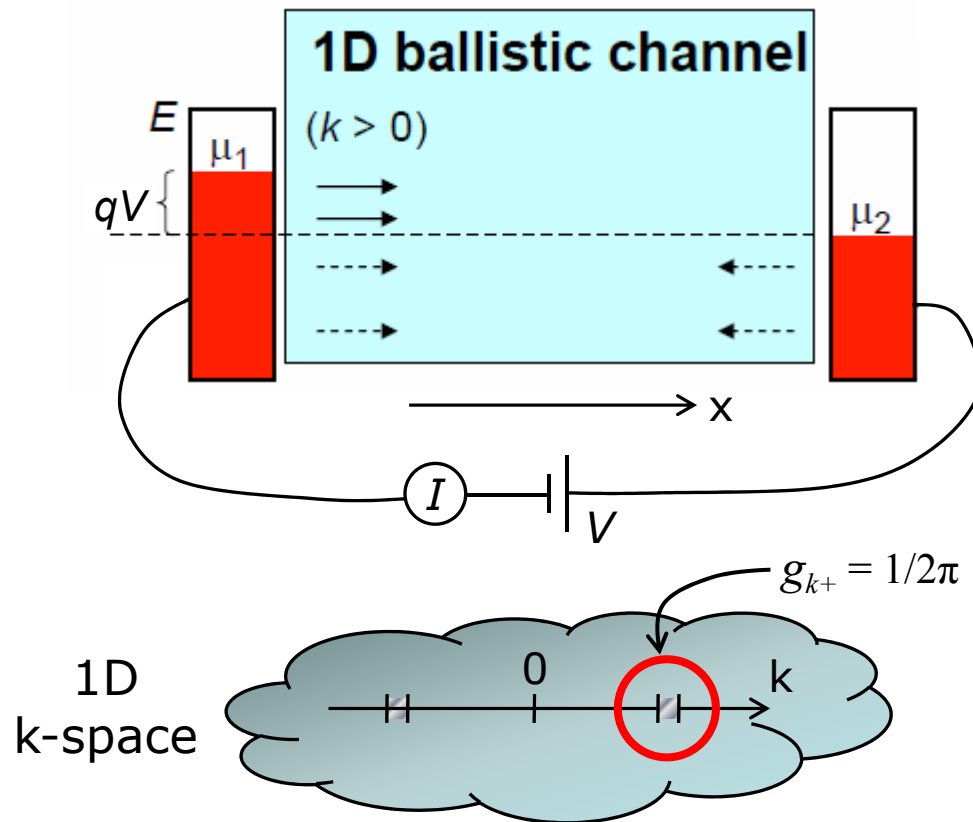
$$I = \frac{2q}{h} \int f(E)T(E)dE$$



Rolf Landauer (1927-1999)

- Two terminals (S and D) with Fermi levels  $\mu_1$  and  $\mu_2$
- S and D are big, ideal electron reservoirs, MANY k-modes
- Transmission channel has only ONE mode,  $M = 1$

# Conductance of 1-D Quantum Wire



$$I = q \int_k (g_k f_k) T_k v_k dk$$

$v = \frac{1}{\hbar} \frac{dE}{dk}$

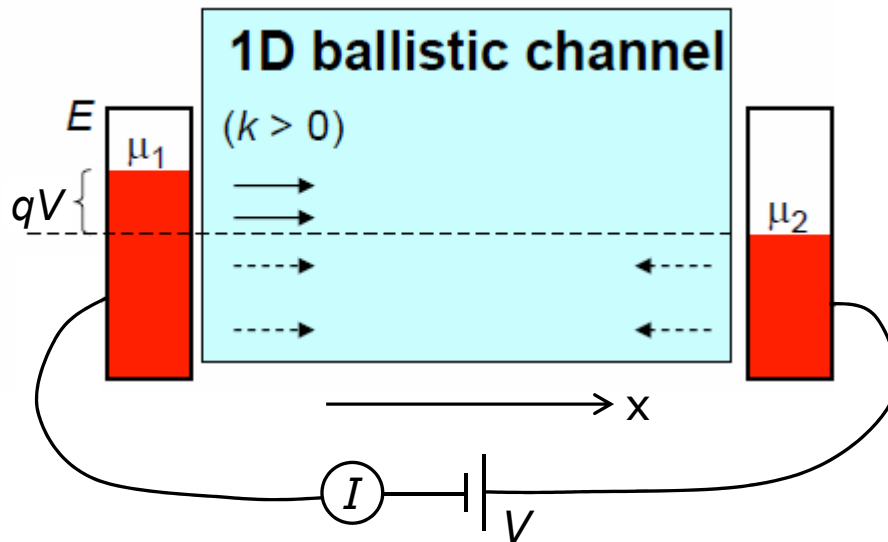
$$I = \frac{q}{h} \int_{\mu_2}^{\mu_1} f_1(E) T(E) dE$$

$$G = \frac{I}{V} = \frac{q^2}{h}$$

x2 spin  
quantum of electrical conductance (per spin per mode)

- Voltage applied is Fermi level separation:  $qV = \mu_1 - \mu_2$
- Channel = 1D, ballistic, coherent, no scattering ( $T=1$ )

# Simple “Proof” by Uncertainty Principle



Current & voltage in quantum channel are

$$I = \frac{q}{\tau} \quad V = \frac{E}{q}$$

where  $\tau$  is the transit time.

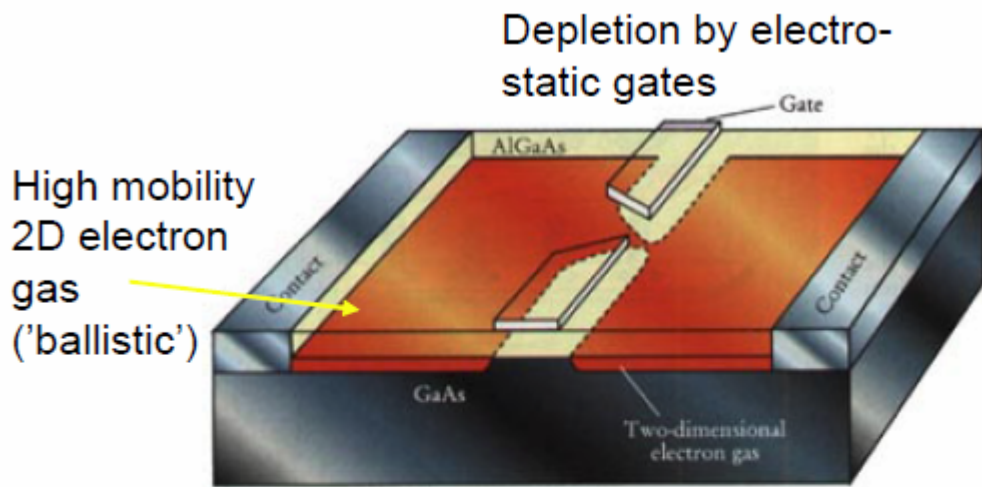
Thus, by Heisenberg Uncertainty Principle:

$$G = \frac{I}{V} = \frac{q^2}{E\tau} = \frac{q^2}{h} \approx \frac{1}{25.8 \text{ k}\Omega}$$

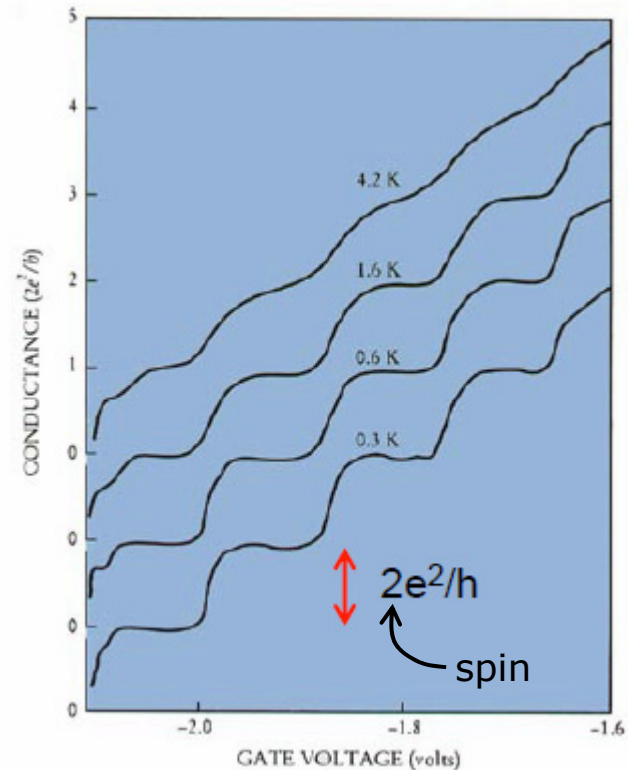
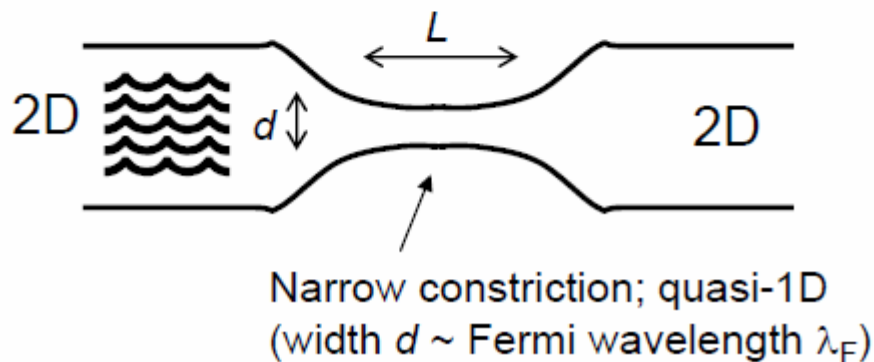
- Note this is for one electron, one (ballistic) quantum channel
- Real resistors can have more quantum channels ( $M$ )
- Conversely, scattering can increase resistance ( $T < 1$ )

# Quasi-1D Channel in 2D Structure

Van Wees et al., *Phys. Rev. Lett.* 60, 848 (1988)



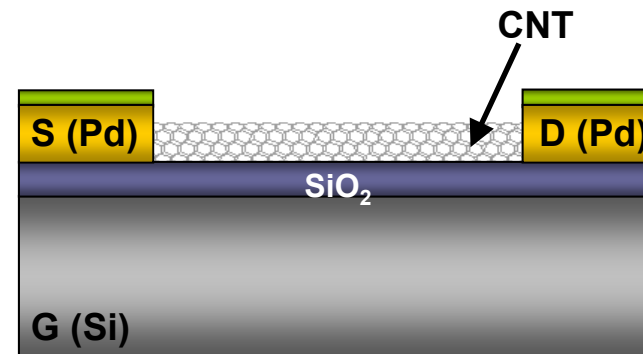
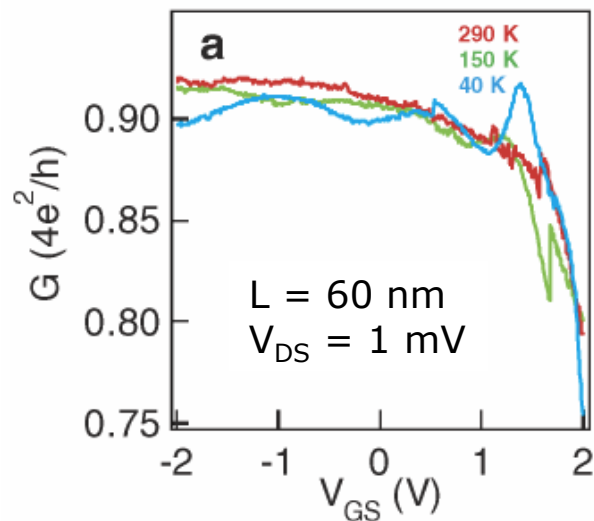
**'Quantum Point Contact'**



Limited conductance  $2e^2/h$  even without scattering, regardless of length  $L$ : "contact resistance"

# Quantum Conductance in Nanotubes

- 2x sub-bands in nanotubes, and 2x from spin
- “Best” conductance of  $4q^2/h$ , or lowest  $R = 6,453 \Omega$
- In practice we measure higher resistance, due to scattering, defects, imperfect contacts (Schottky barriers)

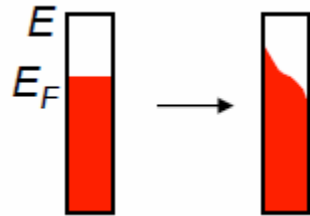


Javey et al., *Phys. Rev. Lett.* (2004)



# Finite Temperatures

- Electrons in leads according to Fermi-Dirac distribution



$$f(E, E_F) = \frac{1}{\exp\left(\frac{E - E_F}{k_B T}\right) + 1}$$

- Conductance with  $n$  channels, at finite temperature  $T$ :

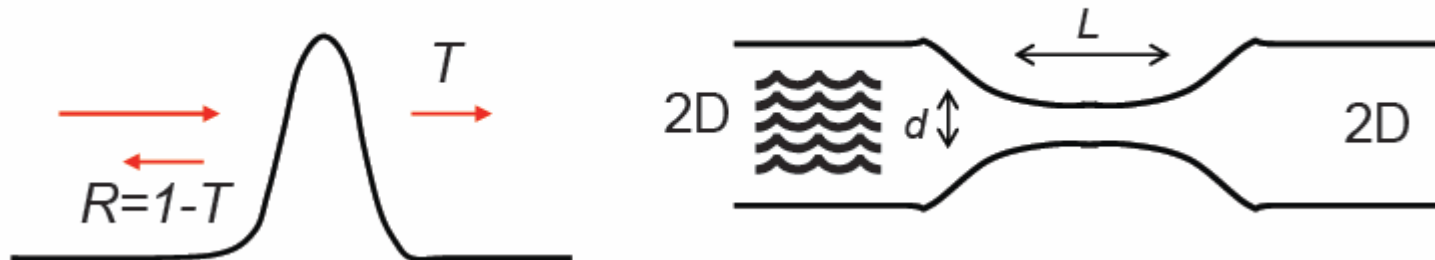
$$G(E_F, T) = \frac{2e^2}{h} \sum_n \int T_n(E) \left(-\frac{df}{dE}\right) dE \approx \frac{2e^2}{h} \sum_n f(E_n - E_F)$$

- At even higher  $T$ : “usual” incoherent transport (dephasing due to inelastic scattering, phonons, etc.)

# Where Is the Resistance?

S. Datta, "Electronic Transport in Mesoscopic Systems" (1995)

One-channel case again:



$$G = \frac{2e^2}{h} T \quad (\text{transmission probability } T)$$

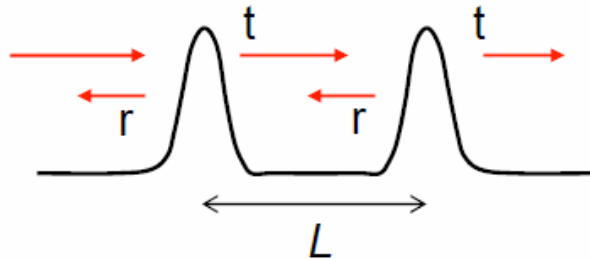
$$\text{Resistance} = \frac{h}{2e^2} \frac{1}{T} = \frac{h}{2e^2} \left( 1 + \frac{1-T}{T} \right) = \boxed{\frac{h}{2e^2}} + \boxed{\frac{h}{2e^2} \frac{R}{T}} \quad (T + R = 1)$$

↑
scattering from barriers  
(zero for perfect conductor)

↑
quantized contact resistance

# Multiple Barriers, Coherent Transport

Two identical barriers in series:

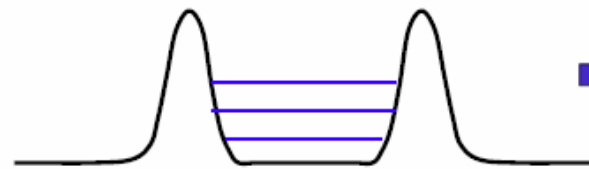


- Coherent, resonant transport
- $L < L_\phi$  (phase-breaking length); electron is truly a wave

- Perfect transmission through resonant, quasi-bound states:

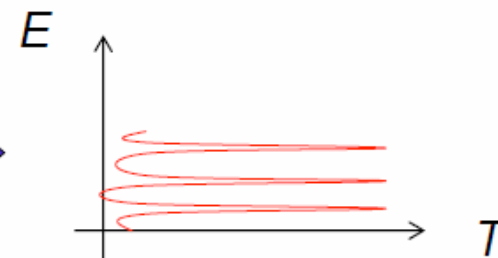
**Quasi-bound states:**  
(‘electron-in-a-box’)

$$kL = \pi n$$



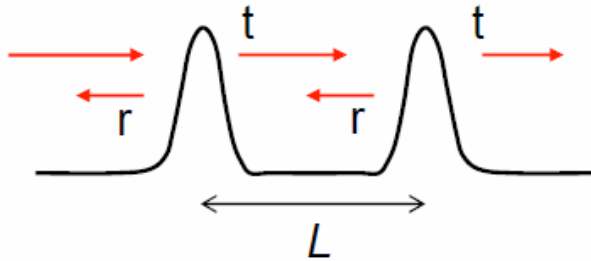
Spectrum  
(0D system)

**Resonant transmission:**



Transport measurement

# Multiple Barriers, Incoherent Transport



- $L > L_\phi$  (phase-breaking length); electron phase gets randomized at, or between scattering sites

- Total transmission (no interference term):

$$T_{\text{total}} = \frac{|t_1|^2 |t_2|^2}{1 - |r_1|^2 |r_2|^2}$$

average mean free path; remember Matthiessen's rule!

- Resistance (scatterers in series):

$$\text{Resistance} = \frac{h}{2e^2} \left( 1 + \frac{|r_1|^2}{|t_1|^2} + \frac{|r_2|^2}{|t_2|^2} + \dots \right) = \frac{h}{2e^2} \left( 1 + \frac{L}{\Lambda} \right)$$

- Ohmic addition of resistances from independent scatterers

# Where Is the Power ( $I^2R$ ) Dissipated?

- Consider, e.g., a single nanotube

- Case I:  $L \ll \Lambda$

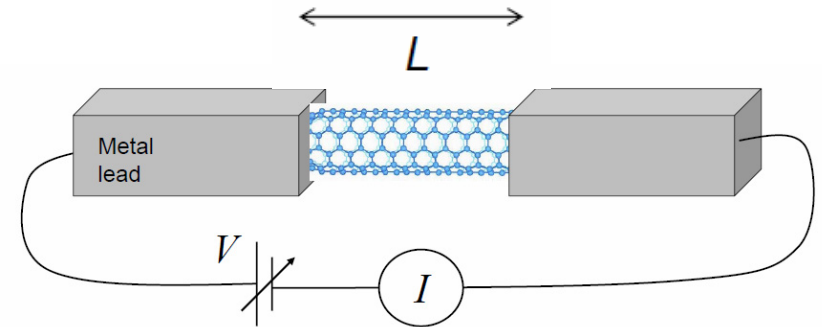
$$R \sim h/4e^2 \sim 6.5 \text{ k}\Omega$$

$$\text{Power } I^2R \rightarrow ?$$

- Case II:  $L \gg \Lambda$

$$R \sim h/4e^2(1 + L/\Lambda)$$

$$\text{Power } I^2R \rightarrow ?$$



- Remember 
$$\frac{1}{\Lambda} \approx \frac{1}{\Lambda_{op.phon.}} + \frac{1}{\Lambda_{ac.phon.}} + \frac{1}{\Lambda_{imp.}} + \frac{1}{\Lambda_{def.}} + \frac{1}{\Lambda_{e-e}}$$

# 1D Wiedemann-Franz Law (WFL)

- Does the WFL hold in 1D? → YES
- 1D ballistic electrons carry energy too, what is their equivalent thermal conductance?

$$G_{th} = L\sigma_e T = \left(\frac{\pi^2 k_B^2}{3e^2}\right) \left(\frac{e^2}{h}\right) T = \frac{\pi^2 k_B^2 T}{3h} \quad (\text{x2 if electron spin included})$$

$$G_{th} \approx 0.28 \text{ nW/K at } 300 \text{ K}$$

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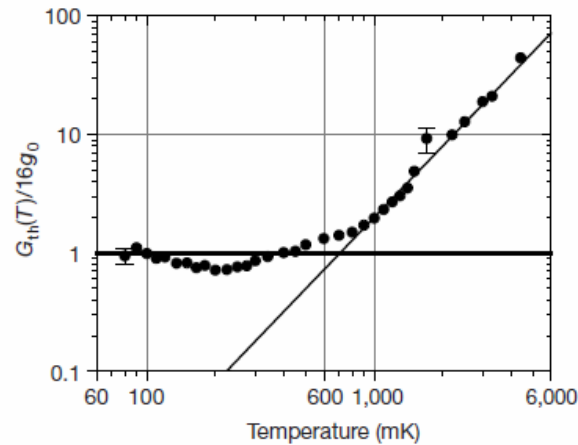
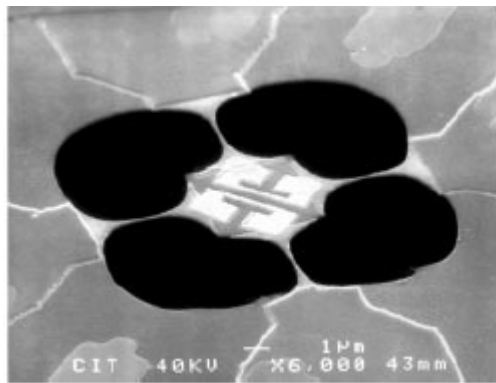
## Thermal Conductivity and Lorenz Number for One-Dimensional Ballistic Transport

We study the thermal conductivity and Lorenz number of charge carriers for one-dimensional ballistic transport within the correlation function formalism. The carrier transit time between two ideal contacts is found to substitute for the collision time in the definition of a ballistic thermal conductivity. A universal thermal conductance  $K = 2\pi^2 k_B^2 T/3h$  is naturally obtained for the degenerate case.

Greiner, Phys. Rev. Lett. (1997)

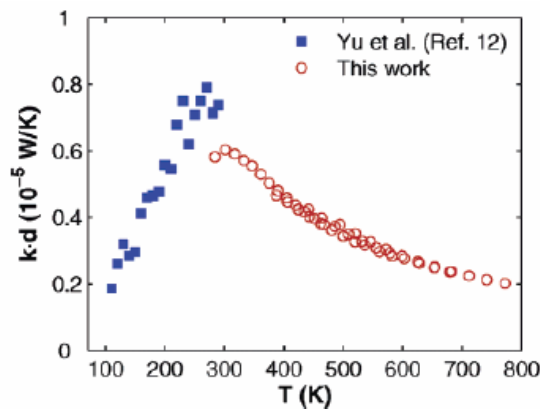
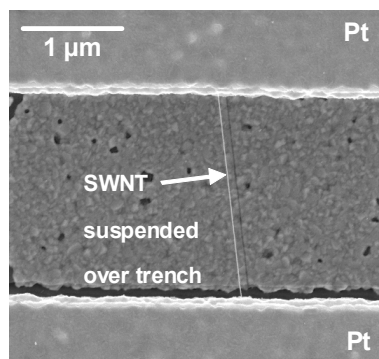
# Phonon Quantum Thermal Conductance

- Same thermal conductance quantum, irrespective of the carrier statistics (Fermi-Dirac vs. Bose-Einstein)



Phonon  $G_{th}$  measurement in GaAs bridge at  $T < 1$  K  
Schwab, *Nature* (2000)

$$G_{th} = \frac{\pi^2 k_B^2 T}{3h} \approx 0.28 \text{ nW/K at } 300 \text{ K}$$



Single nanotube  $G_{th} = 2.4$  nW/K at  $T = 300$  K  
Pop, *Nano Lett.* (2006)

Matlab tip:

```
>> syms x;  
>> int(x^2*exp(x)/(exp(x)+1)^2,0,Inf)  
ans =  
1/6*pi^2
```

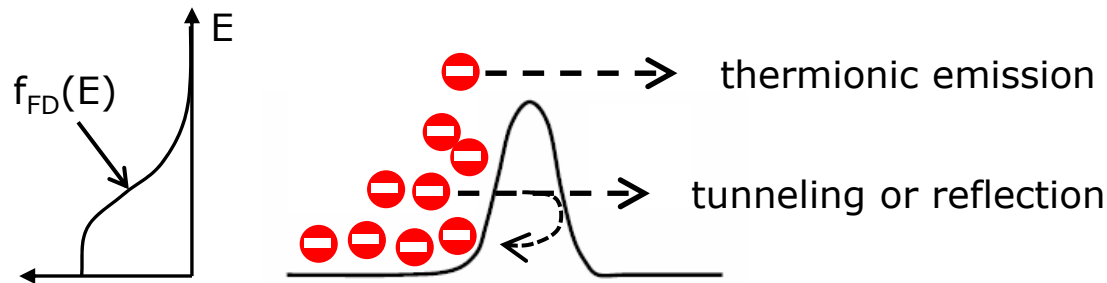
# Electrical vs. Thermal Conductance $G_0$

- Electrical experiments  $\rightarrow$  steps in the conductance (not observed in thermal experiments)
- In electrical experiments the chemical potential (Fermi level) and temperature can be independently varied
  - Consequently, at low-T the sharp edge of the Fermi-Dirac function can be swept through 1-D modes
  - Electrical (electron) conductance quantum:  $G_0 = (dI_e/dV)|_{\text{low } dV}$
- In thermal (phonon) experiments only the temperature can be swept
  - The broader Bose-Einstein distribution smears out all features except the lowest lying modes at low temperatures
  - Thermal (phonon) conductance quantum:  $G_0 = (dQ_{\text{th}}/dT)|_{\text{low } dT}$

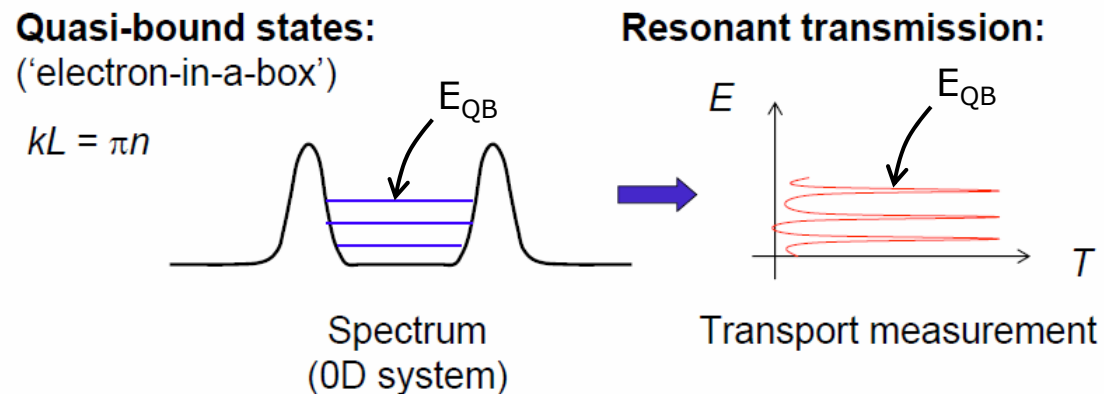


# Back to the Quantum-Coherent Regime

- Single energy barrier – how do you get across?

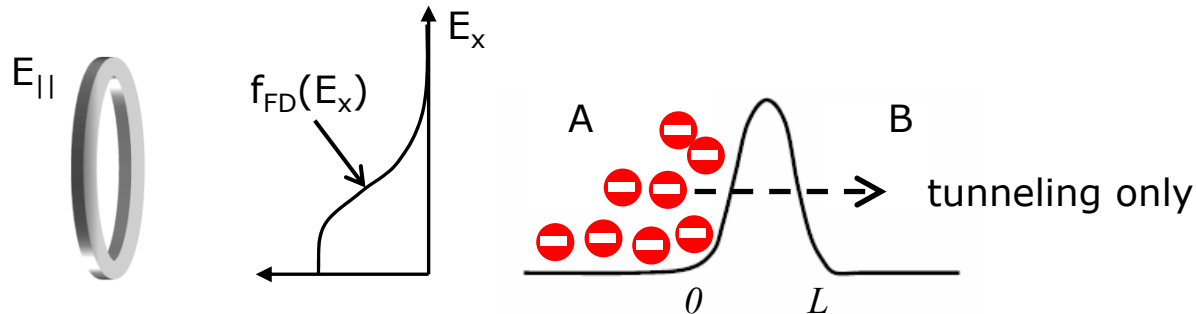


- Double barrier: transmission through quasi-bound (QB) states



- Generally, need  $\lambda \sim L \leq L_\phi$  (phase-breaking length)

# Wentzel-Kramers-Brillouin (WKB)



- Assume smoothly varying potential barrier, no reflections

$$T = \frac{|\psi_{trans.}|^2}{|\psi_{incid.}|^2} \approx \exp\left(-2 \int_0^L |k(x)| dx\right) \quad \text{\textit{k}(x) depends on energy dispersion}$$

$$J_{A \rightarrow B} = (\# \text{incident states}) \int f_A g_A T(E_x) (1 - f_B) g_B dE$$

E.g. in 3D, the net current is:

$$J = J_{A \rightarrow B} - J_{B \rightarrow A} = \frac{qm^*}{2\pi^2 \hbar^3} \int (f_A - f_B) g_A g_B T(E) dE \quad \text{\textit{Fancier version of Landauer formula!}}$$